

N-channel 30 V 17 mΩ logic level MOSFET in TO220 Rev. 2 — 3 April 2012 Product

Product data sheet

Product profile 1.

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1.1 General description

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Quick reference data					
Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	30	V
drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u> -	-	32	А
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	45	W
junction temperature		-55	-	175	°C
aracteristics					
drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 13</u>	-	18.7	23.4	mΩ
	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 13</u>	-	13.4	17	mΩ
characteristics					
gate-drain charge	V _{GS} = 4.5 V; I _D = 10 A; V _{DS} = 15 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	1.94	-	nC
total gate charge	V _{GS} = 4.5 V; I _D = 10 A; V _{DS} = 15 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	5.1	-	nC
e ruggedness					
non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 32 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped	-	-	13	mJ
	Parameter drain-source voltage drain current total power dissipation junction temperature tracteristics drain-source on-state resistance characteristics gate-drain charge total gate charge e ruggedness non-repetitive drain-source	ParameterConditionsdrain-source voltage $T_j \ge 25 ^\circ C; T_j \le 175 ^\circ C$ drain current $T_{mb} = 25 ^\circ C; V_{GS} = 10 V; see Figure 1$ total power dissipation $T_{mb} = 25 ^\circ C; see Figure 2$ junction temperaturetracteristicsdrain-source on-stateresistance $V_{GS} = 4.5 V; I_D = 10 A; T_j = 25 ^\circ C;$ see $Figure 13$ $V_{GS} = 10 V; I_D = 10 A; T_j = 25 ^\circ C;$ see $Figure 13$ characteristicsgate-drain charge $V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V;$ see $Figure 14; see Figure 15$ total gate charge $V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V;$ see $Figure 14; see Figure 15$ total gate charge $V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V;$ see $Figure 14; see Figure 15$ total gate charge $V_{GS} = 10 V; T_j(init) = 25 ^\circ C; I_D = 32 A;$	ParameterConditionsMindrain-source voltage $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ -drain current $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see Figure 1}$ [1]total power dissipation $T_{mb} = 25 \text{ °C}; \text{ see Figure 2}$ -junction temperature-55tracteristics $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ -drain-source on-state resistance $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ -gate-drain charge $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ -gate-drain charge $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 15 \text{ V};$ -see Figure 13 $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 15 \text{ V};$ -see Figure 14; see Figure 15total gate charge $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 15 \text{ V};$ -e ruggednessnon-repetitive drain-source $V_{GS} = 10 \text{ V}; T_j(init) = 25 \text{ °C}; I_D = 32 \text{ A};$ -	ParameterConditionsMinTypdrain-source voltage $T_j \ge 25 ^{\circ}C; T_j \le 175 ^{\circ}C$ drain current $T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V; see Figure 1$ [1]total power dissipation $T_{mb} = 25 ^{\circ}C; see Figure 2$ junction temperature-55aracteristics $V_{GS} = 4.5 V; I_D = 10 A; T_j = 25 ^{\circ}C;$ -18.7drain-source on-state $V_{GS} = 4.5 V; I_D = 10 A; T_j = 25 ^{\circ}C;$ -13.4see Figure 13 $V_{GS} = 10 V; I_D = 10 A; T_j = 25 ^{\circ}C;$ -13.4characteristics-1.94gate-drain charge $V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V;$ -5.1total gate charge $V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V;$ -5.1e ruggednessnon-repetitive drain-source $V_{GS} = 10 V; T_{j(init)} = 25 ^{\circ}C; I_D = 32 A;$	ParameterConditionsMinTypMaxdrain-source voltage $T_j \ge 25 ^\circ$ C; $T_j \le 175 ^\circ$ C30drain current $T_{mb} = 25 ^\circ$ C; $V_{GS} = 10 ^\circ$ V; see Figure 1[1]32total power dissipation $T_{mb} = 25 ^\circ$ C; see Figure 245junction temperature-55-175aracteristicsdrain-source on-state resistance $V_{GS} = 4.5 ^\circ$ V; $I_D = 10 ^\circ$; $T_j = 25 ^\circ$ C; see Figure 13-18.723.4 $V_{GS} = 10 ^\circ$ V; $I_D = 10 ^\circ$; $T_j = 25 ^\circ$ C; see Figure 13-13.417characteristicsgate-drain charge $V_{GS} = 4.5 ^\circ$ V; $I_D = 10 ^\circ$; $V_{DS} = 15 ^\circ$ see Figure 14; see Figure 15-1.94-total gate charge $V_{GS} = 4.5 ^\circ$; $I_D = 10 ^\circ$; $V_{DS} = 15 ^\circ$; see Figure 14; see Figure 15-5.1-e ruggedness non-repetitive drain-source $V_{GS} = 10 ^\circ$; $T_{j(init)} = 25 ^\circ$ C; $I_D = 32 ^\circ$;-13

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN017-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

SOT78 (TO-220AB)

4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
V _{GS}	gate-source voltage			-20	20	V
ID	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	[1]	-	26.9	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	32	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	152	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	45	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
ls	source current	T _{mb} = 25 °C		-	32	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	152	А
Avalanche i	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ I}_{D} = 32 \text{ A};$ $V_{sup} \leq 30 \text{ V}; \text{ R}_{GS} = 50 \Omega; \text{ unclamped}$		-	13	mJ

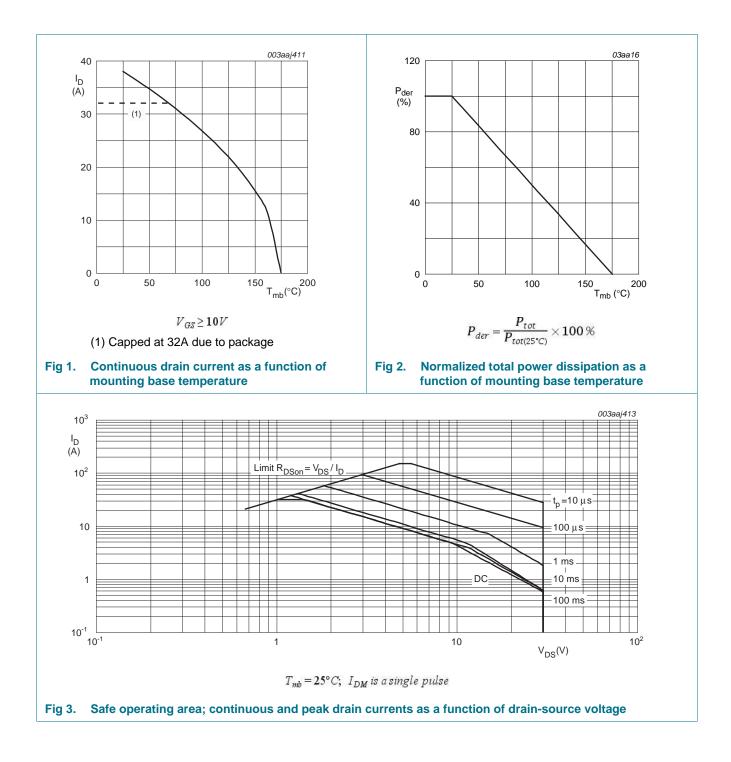
[1] Continuous current is limited by package.

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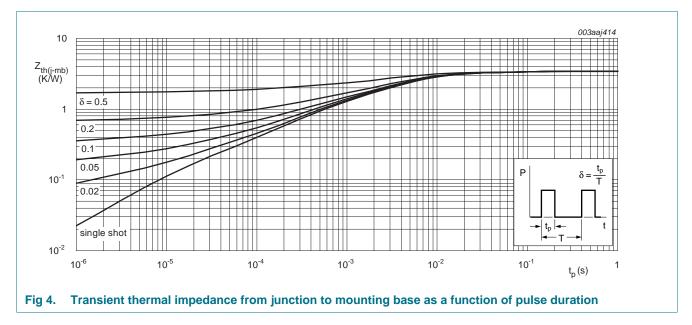
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	3.24	3.31	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



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6. Characteristics

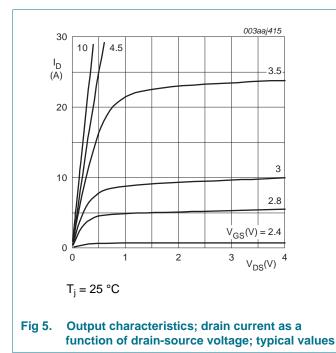
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 11	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	2.45	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	0.3	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 125 °C	-	-	50	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 10 A; T _j = 175 °C; see <u>Figure 12</u>	-	-	43.2	mΩ
		V_{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; see Figure 13	-	18.7	23.4	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; see <u>Figure 12</u>	-	24	31.5	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 100 °C; see <u>Figure 12</u>	-	-	23.5	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; see <u>Figure 13</u>	-	13.4	17	mΩ
R _G	gate resistance	f = 1 MHz	-	2.03	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	10.7	-	nC
		$I_D = 0 A$; $V_{DS} = 0 V$; $V_{GS} = 10 V$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	9.55	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15	-	5.1	-	nC
Q _{GS}	gate-source charge	$I_{D} = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	1.52	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	1	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.5	-	nC
Q _{GD}	gate-drain charge		-	1.94	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	2.86	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	552	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	127	-	pF
C _{rss}	reverse transfer capacitance		-	64	-	pF

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Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 1.5 Ω; V_{GS} = 4.5 V;	-	10.7	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		9.2	-	ns
t _{d(off)}	turn-off delay time		-	11.4	-	ns
t _f	fall time			5.1	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.89	1.2	V
t _{rr}	reverse recovery time	I _S = 10 A; dI _S /dt = -100 A/µs;	-	17.3	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	6.5	-	nC



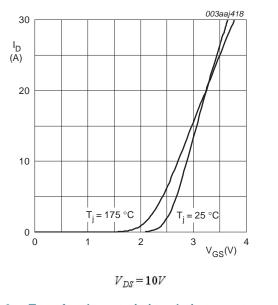
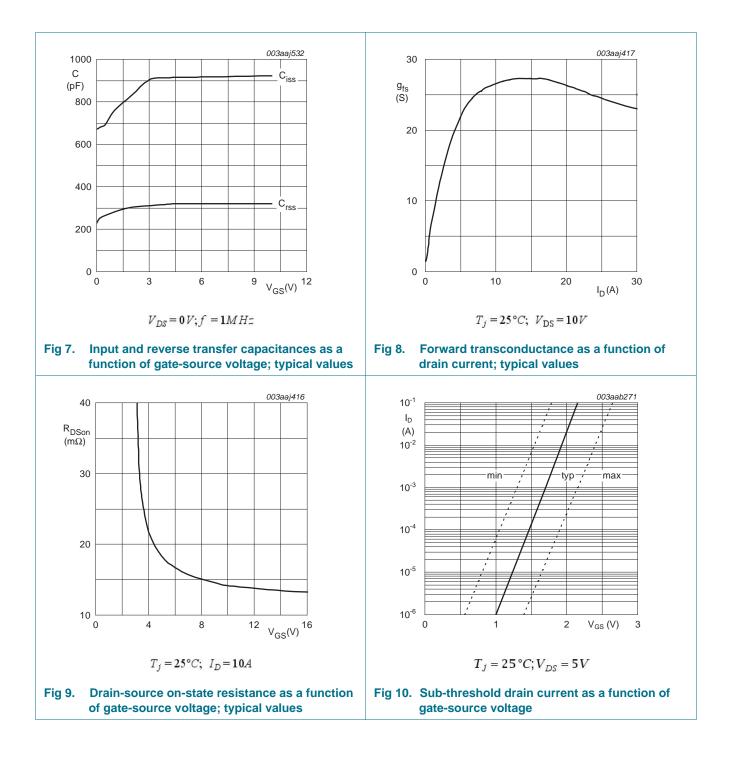


Fig 6. Transfer characteristics; drain current as a function of gate-source voltage; typical values

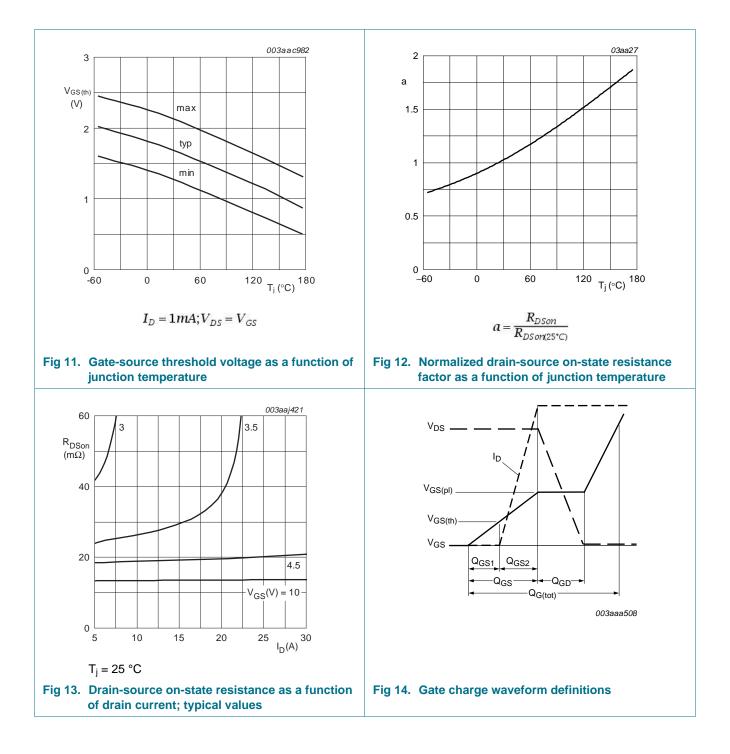
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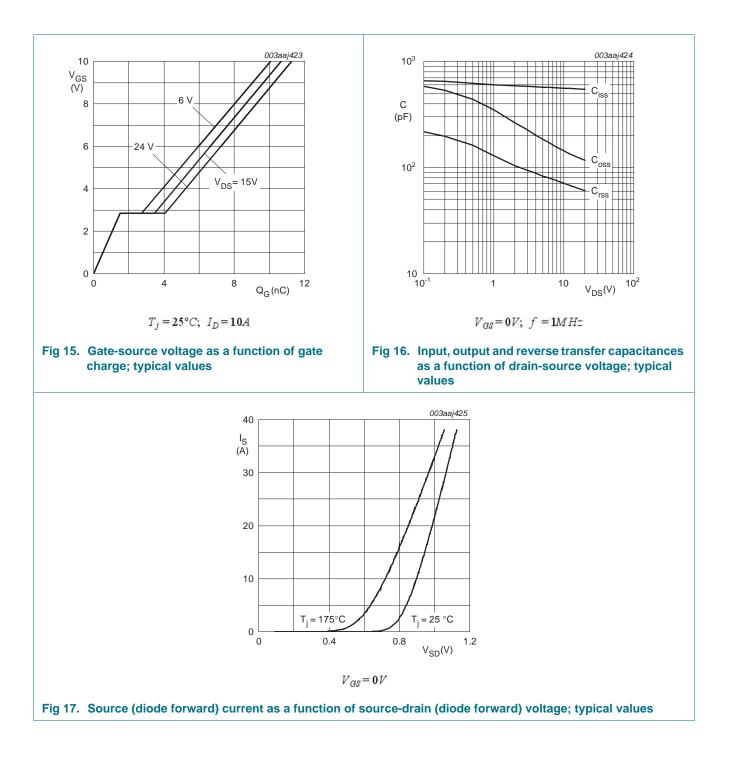


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7. Package outline

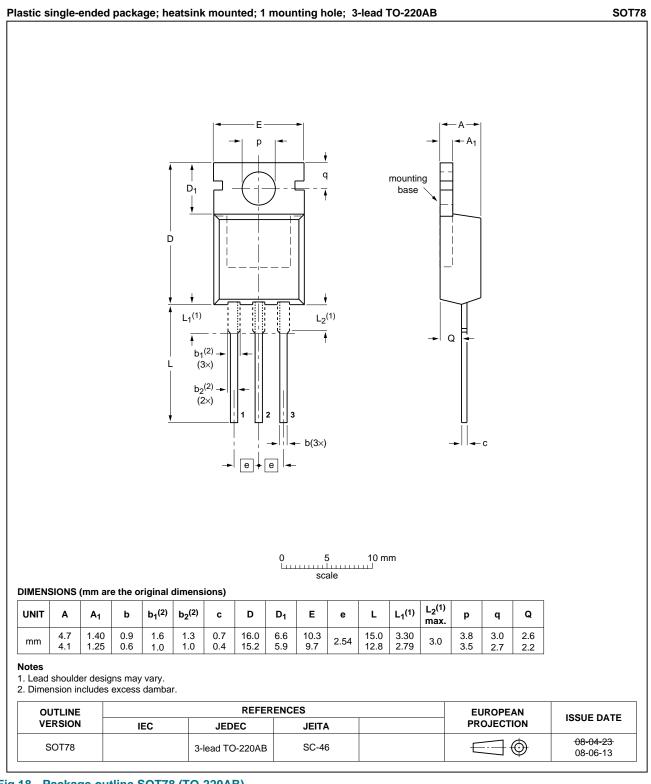


Fig 18. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision I	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN017-30PL v.2	20120403	Product data sheet	-	PSMN017-30PL v.1
Modifications:	 Status change 	d from objective to product.		
	 Various chang 	es to content.		
PSMN017-30PL v.1	20120228	Objective data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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